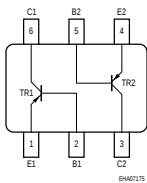


PNP Silicon AF Transistor Arrays

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated transistor with good matching in one package
- BC856S / U, BC857S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



BC856S/U BC857S



Type	Marking	Pin Configuration						Package
BC856S	3Ds	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BC856U	3Ds	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74
BC857S	3Cs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC856S/U BC857S	V_{CEO}	65 45	-
Collector-base voltage BC856S, BC856U BC857S	V_{CBO}	80 50	V
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation- $T_S \leq 115$ °C, BC856S $T_S \leq 118$ °C, BC856U, BC857U	P_{tot}	250 250	-
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BC856S, BC857S BC856U	R_{thJS}	≤ 140 ≤ 130	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

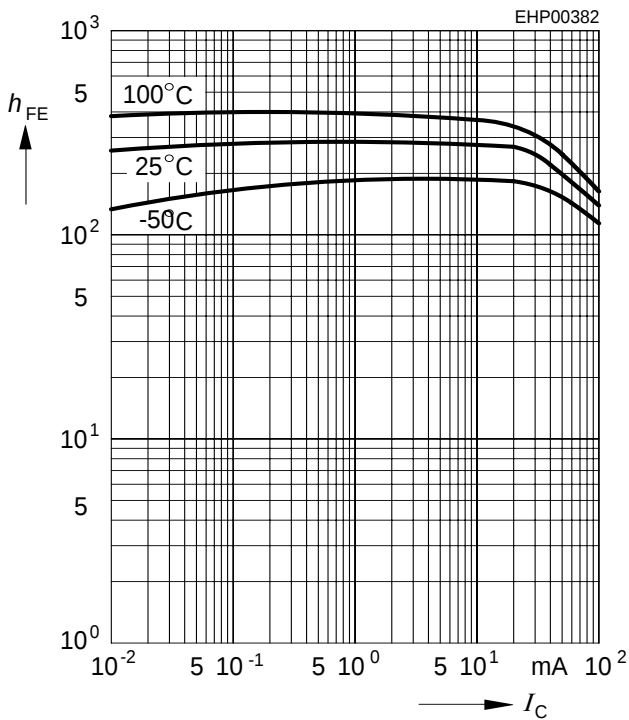
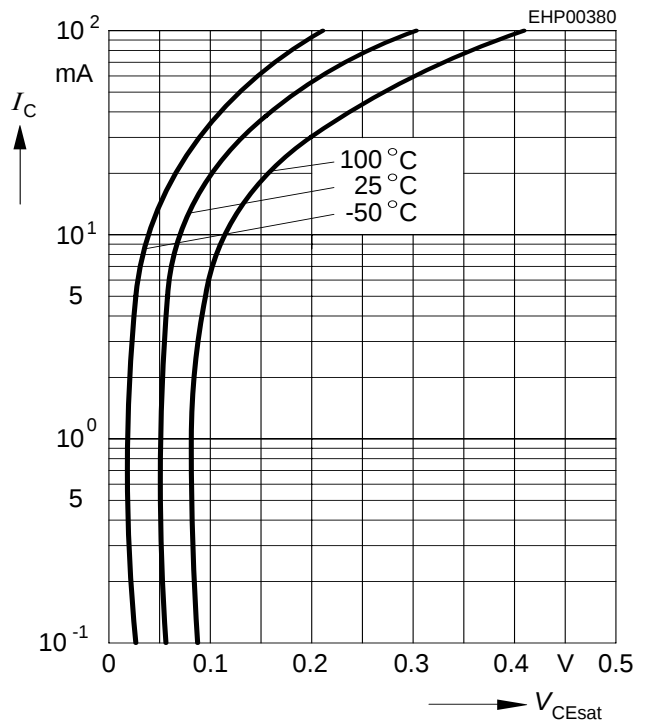
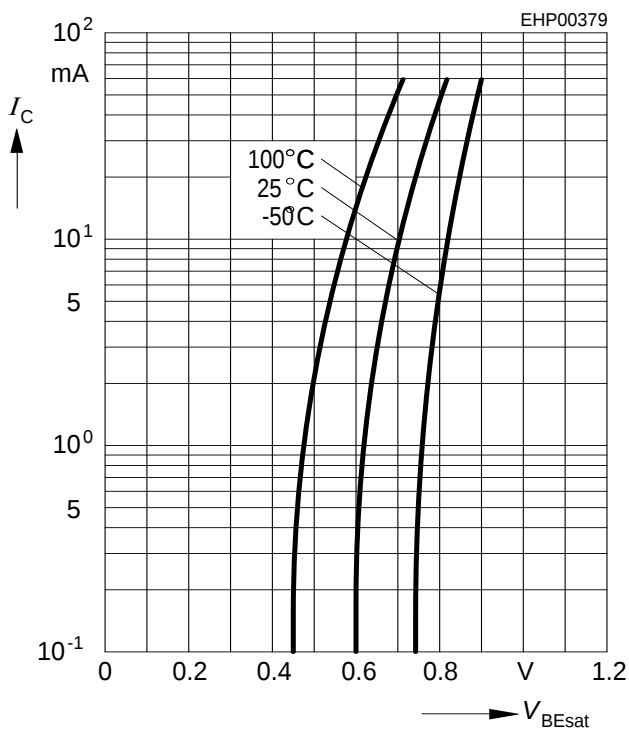
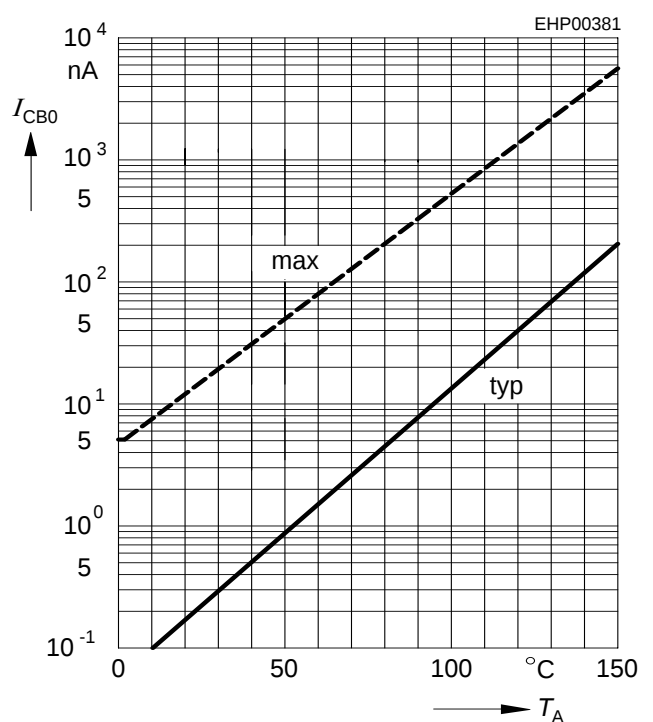
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$, BC856S/U $I_C = 10\text{ mA}$, $I_B = 0$, BC857S	$V_{(BR)CEO}$	65 45	- -	- -	-	
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC856S/U $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC857S	$V_{(BR)CBO}$	80 50	- -	- -		
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	5	-	-		V
Collector-base cutoff current $V_{CB} = 45\text{ V}$, $I_E = 0$ $V_{CB} = 45\text{ V}$, $I_E = 0$, $T_A = 150\text{ }^{\circ}\text{C}$	I_{CBO}	- -	- -	0.015 5		μA
DC current gain ¹⁾ $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$	h_{FE}	- 200	250 290	- 630	-	
Collector-emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	75 250	300 650	mV	
Base emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	700 850	- -	-	
Base-emitter voltage ¹⁾ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	600 -	650 -	750 820	mV	

¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

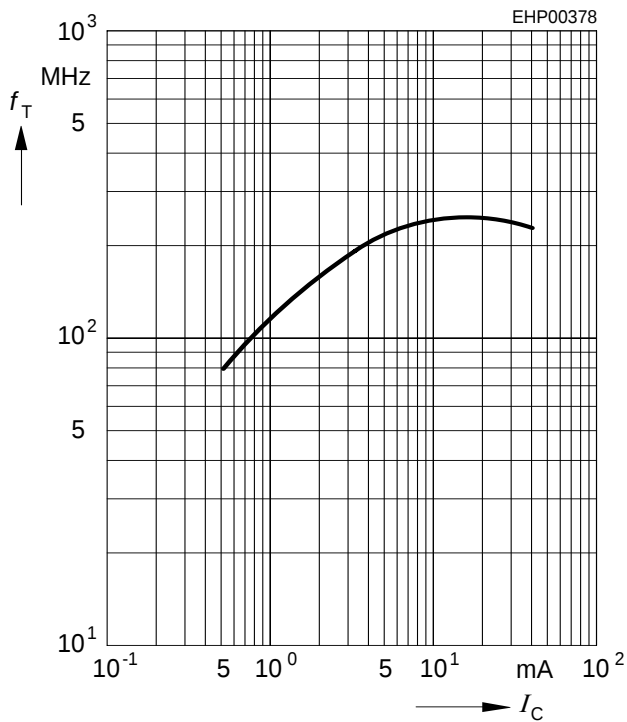
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 20\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{11e}	-	4.5	-	kΩ
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{12e}	-	2	-	10 ⁻⁴
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{21e}	-	330	-	-
Open-circuit output admittance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{22e}	-	30	-	μS
Noise figure $I_C = 200\text{ μA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$, $\Delta f = 200\text{ Hz}$, $R_S = 2\text{ kΩ}$	F	-	-	10	dB

DC current gain $h_{FE} = f(I_C)$
 $V_{CE} = 5 \text{ V}$

Collector-emitter saturation voltage
 $I_C = f(V_{CEsat}), h_{FE} = 20$

Base-emitter saturation voltage
 $I_C = f(V_{BEsat}), h_{FE} = 20$

Collector cutoff current $I_{CBO} = f(T_A)$
 $V_{CBO} = 30 \text{ V}$


Transition frequency $f_T = f(I_C)$

$V_{CE} = 5\text{ V}$



Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

BC856S, BC857S



Total power dissipation $P_{tot} = f(T_S)$

BC856U



Permissible Pulse Load $R_{thJS} = f(t_p)$

BC856S; BC857S


Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

BC856S, BC857S


Permissible Puls Load $R_{thJS} = f(t_p)$

BC856U


Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

BC856U



Package Outline



Foot Print



Marking Layout (Example)

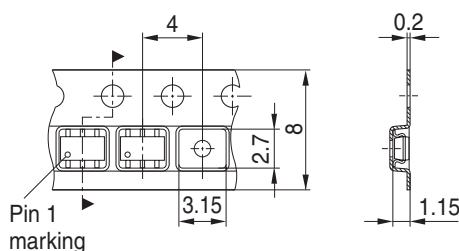
Small variations in positioning of Date code, Type code and Manufacture are possible.



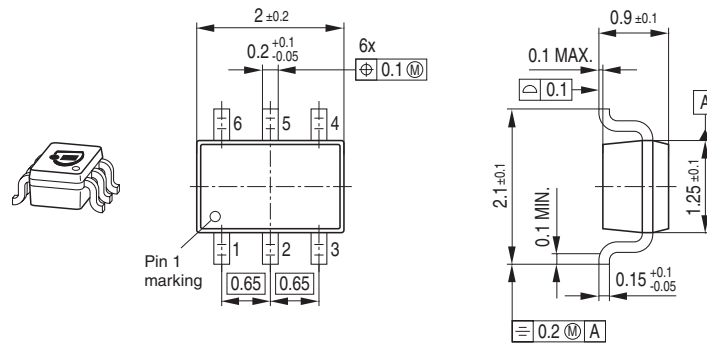
Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

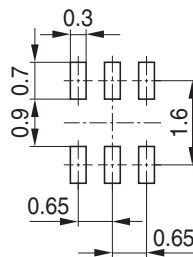
For symmetric types no defined Pin 1 orientation in reel.



Package Outline

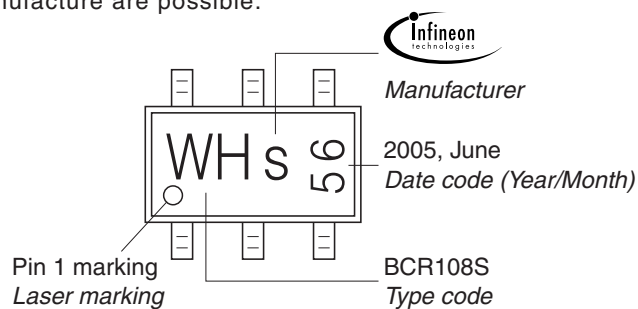


Foot Print



Marking Layout (Example)

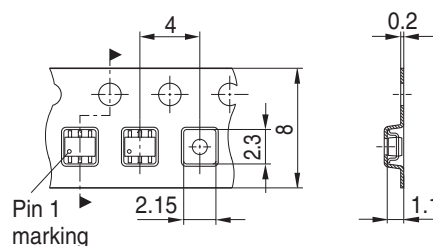
Small variations in positioning of
Date code, Type code and Manufacture are possible.



Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
Reel $\varnothing 330$ mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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